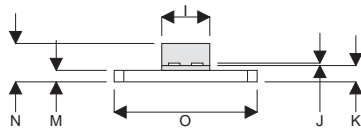
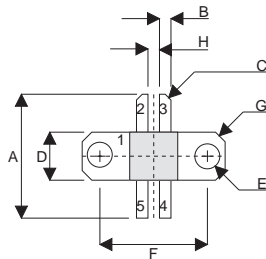


MECHANICAL DATA



DQ

PIN 1 SOURCE (COMMON) PIN 2 DRAIN 1  
 PIN 3 DRAIN 2 PIN 4 GATE 2  
 PIN 5 GATE 1

DIM	mm	Tol.	Inches	Tol.
A	16.38	0.26	0.645	0.010
B	1.52	0.13	0.060	0.005
C	45°	5°	45°	5°
D	6.35	0.13	0.250	0.005
E	3.30	0.13	0.130	0.005
F	14.22	0.13	0.560	0.005
G	1.27 x 45°	0.13	0.05 x 45°	0.005
H	1.52	0.13	0.060	0.005
I	6.35	0.13	0.250	0.005
J	0.13	0.02	0.005	0.001
K	2.16	0.13	0.085	0.005
M	1.52	0.13	0.060	0.005
N	5.08	MAX	0.200	MAX
O	18.90	0.13	0.744	0.005

**GOLD METALLISED  
 MULTI-PURPOSE SILICON  
 DMOS RF FET  
 10W – 28V – 1GHz  
 PUSH-PULL**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- VERY LOW  $C_{rss}$
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 10 dB MINIMUM

APPLICATIONS

- VHF/UHF COMMUNICATIONS  
 from 50 MHz to 1 GHz

ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$P_D$	Power Dissipation	58W
$BV_{DSS}$	Drain – Source Breakdown Voltage *	65V
$BV_{GSS}$	Gate – Source Breakdown Voltage *	$\pm 20V$
$I_{D(sat)}$	Drain Current *	2A
$T_{stg}$	Storage Temperature	-65 to 150°C
$T_j$	Maximum Operating Junction Temperature	200°C

\* Per Side

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>PER SIDE</b>					
B <sub>V</sub> DSS	Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0      I <sub>D</sub> = 10mA	65		V
I <sub>D</sub> DSS	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 28V      V <sub>GS</sub> = 0		2	mA
I <sub>G</sub> DSS	Gate Leakage Current	V <sub>GS</sub> = 20V      V <sub>DS</sub> = 0		1	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage*	I <sub>D</sub> = 10mA      V <sub>DS</sub> = V <sub>GS</sub>	1	7	V
g <sub>fs</sub>	Forward Transconductance*	V <sub>DS</sub> = 10V      I <sub>D</sub> = 2A	0.36		S
<b>TOTAL DEVICE</b>					
G <sub>PS</sub>	Common Source Power Gain	P <sub>O</sub> = 10W	10		dB
η	Drain Efficiency	V <sub>DS</sub> = 28V      I <sub>DQ</sub> = 0.4A	40		%
V <sub>SWR</sub>	Load Mismatch Tolerance	f = 1GHz	20:1		—
<b>PER SIDE</b>					
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 28V      V <sub>GS</sub> = -5V      f = 1MHz		24	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 28V      V <sub>GS</sub> = 0      f = 1MHz		12	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>DS</sub> = 28V      V <sub>GS</sub> = 0      f = 1MHz		1	pF

\* Pulse Test:    Pulse Duration = 300 μs , Duty Cycle ≤ 2%

### HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

### THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 3.0°C / W
-----------------------	------------------------------------	----------------